

Low voltage fast-switching NPN power transistor

Features

- Very low collector-emitter saturation voltage
- High current gain characteristic
- Fast switching speed
- Miniature SOT-23 plastic package for surface mounting circuits

Applications

- LED
- Battery charger
- Voltage and relay driver
- Voltage regulation



The 2STR1215 is a NPN transistor manufactured using new "PB-HCD" (Power Bipolar High Current Density) technology. The resulting transistor shows exceptional high gain performances coupled with very low saturation voltage. The complementary PNP is the 2STR2215.

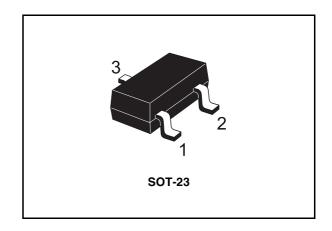


Figure 1. Internal schematic diagram

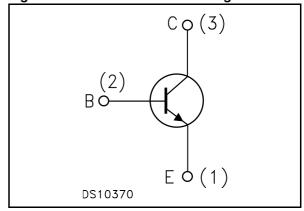


Table 1. Device summary

| Order code | Marking | Package | Packaging |
|------------|---------|---------|---------------|
| 2STR1215 | 115 | SOT-23 | Tape and reel |

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2STR1215 Electrical ratings

1 Electrical ratings

Table 2. Absolute maximum rating

| Symbol | Parameter | Value | Unit |
|------------------|--|-------|------|
| V_{CBO} | Collector-base voltage (I _E = 0) | 15 | V |
| V _{CEO} | Collector-emitter voltage (I _B = 0) | 15 | V |
| V _{EBO} | Emitter-base voltage ($I_C = 0$) | 5 | V |
| I _C | Collector current | 1.5 | Α |
| I _{CM} | Collector peak current (t _P < 5 ms) | 3 | Α |
| P _{tot} | Total dissipation at T _{amb} = 25 °C | 0.5 | W |
| T _{stg} | Storage temperature -65 | | °C |
| T _J | Max. operating junction temperature | 150 | °C |

Table 3. Thermal data

| Symbol | Parameter | Value | Unit |
|-------------------------------------|-------------------------------------|-------|------|
| R _{thj-amb} ⁽¹⁾ | Thermal resistance junction-amb max | 250 | °C/W |

(1) Device mounted on PCB area of $1\,\mathrm{cm}^2$

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Electrical characteristics 2STR1215

2 Electrical characteristics

 $(T_{case} = 25^{\circ}C \text{ unless otherwise specified})$

Table 4. Electrical characteristics

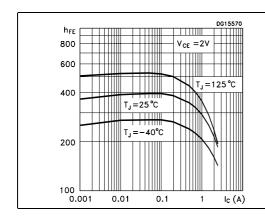
| Symbol | Parameter | Test conditions | Min. | Тур. | Max. | Unit |
|-------------------------------------|--|--|-------------------------|-------------|---------------------|-------------|
| I _{CBO} | Collector cut-off current (I _E =0) | V _{CB} = 15 V | | | 0.1 | μΑ |
| I _{EBO} | Emitter cut-off current (I _C =0) | V _{EB} = 4 V | | | 0.1 | μА |
| V _{(BR)CBO} | Collector-base breakdown voltage (I _E = 0) | I _C = 100 μA | 15 | | | V |
| V _{(BR)CEO} (1) | Collector-emitter breakdown voltage (I _B = 0) | I _C = 10 mA | 15 | | | V |
| V _{(BR)EBO} | Emitter-base breakdown voltage (I _C = 0) | I _E = 100 μA | 5 | | | V |
| V _{CE(sat)} (1) | Collector-emitter saturation voltage | $I_C = 0.1 \text{ A}$ $I_B = 1 \text{mA}$ $I_C = 1 \text{ A}$ $I_B = 100 \text{ mA}$ $I_C = 2 \text{ A}$ $I_B = 200 \text{ mA}$ | | 0.25 0.4 | 0.15 0.5 0.85 | V V V |
| V _{BE(sat)} (1) | Base-emitter saturation voltage | I _C = 1 A I _B = 100 mA | | 0.9 | 1.25 | V |
| h _{FE} ⁽¹⁾ | DC current gain | $\begin{split} & I_{C} = 50 \text{ mA} & V_{CE} = 2 \text{ V} \\ & I_{C} = 0.5 \text{ A} & V_{CE} = 2 \text{ V} \\ & I_{C} = 1 \text{ A} & V_{CE} = 2 \text{ V} \\ & I_{C} = 2 \text{ A} & V_{CE} = 2 \text{ V} \end{split}$ | 200 200 130 80 | 280 | 560 | |
| C _{CBO} | Collector-base capacitance (I _E = 0) | V _{CB} = 10 V | | 16 | | pF |
| t _{on} t _{off} | Resistive load Turn-on time Turn-off time | $I_C = 1.5 \text{ A}$ $V_{CC} = 10 \text{ V}$ $I_{B1} = -I_{B2} = 150 \text{ mA}$ | | 60 310 | | ns ns |

^{1.} Pulsed duration = 300 µs, duty cycle ≤1.5%

2.1 Electrical characteristics (curves)

Figure 2. DC current gain

Figure 3. Collector-emitter saturation voltage



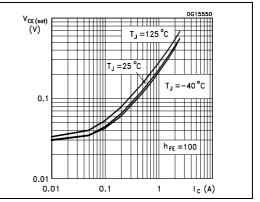
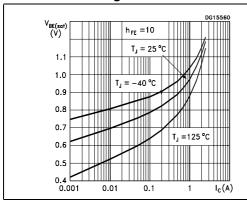


Figure 4. Base-emitter saturation voltage

Figure 5. Resistive load switching time



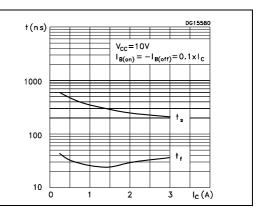
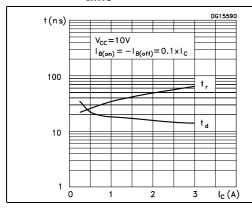
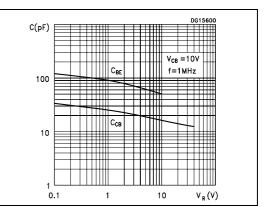


Figure 6. Resistive load switching time

Figure 7. Capacitance

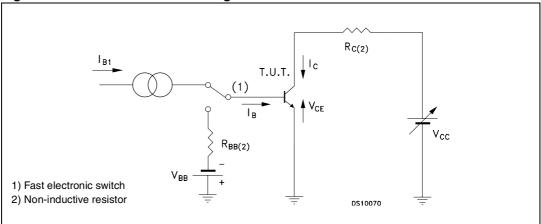




Electrical characteristics 2STR1215

2.2 Test circuits

Figure 8. Resistive load switching test circuit



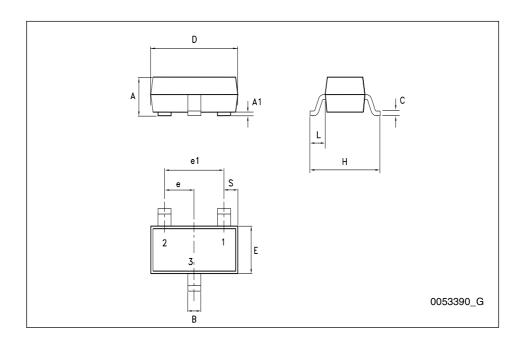
3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

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| SO | 1-23 | mech | anıc | al data |
|----|------|------|------|---------|

| DIM. | mm. | | | | |
|------|-------|-----|------|--|--|
| DIW. | min. | typ | max. | | |
| А | 0.89 | | 1.4 | | |
| A1 | 0 | | 0.1 | | |
| В | 0.3 | | 0.51 | | |
| С | 0.085 | | 0.18 | | |
| D | 2.75 | | 3.04 | | |
| е | 0.85 | | 1.05 | | |
| e1 | 1.7 | | 2.1 | | |
| Е | 1.2 | | 1.6 | | |
| Н | 2.1 | | 2.75 | | |
| L | | 0.6 | | | |
| S | 0.35 | | 0.65 | | |



2STR1215 Revision history

4 Revision history

Table 5. Document revision history

| Date | Revision | Changes |
|-------------|----------|-------------------------------------|
| 09-Feb-2006 | 1 | Initial release |
| 18-Jul-2006 | 2 | New template |
| 08-Sep-2008 | 3 | Updated the SOT-23 mechanical data. |

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